BT139X series H

GENERAL DESCRIPTION

Glass passivated triacs in a full pack, plastic envelope, intended for use in applications requiring high noise immunity in addition to high, bidirectional blocking voltage capability and thermal cycling performance. Typical applications include motor control, industrial lighting, heating and static switching.

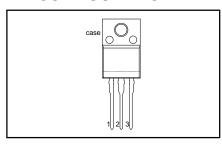
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V_{DRM}	BT139X- Repetitive peak off-state voltages	500H 500	600H 600	800H 800	V
I _{T(RMS)} I _{TSM}	RMS on-state current Non-repetitive peak on-state current	16 140	16 140	16 140	A A

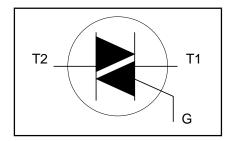
PINNING - SOT186A

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-600 600 ¹	-800 800	V
I _{T(RMS)}	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{hs} \le 38 ^{\circ}\text{C}$ full sine wave; $T_j = 25 ^{\circ}\text{C}$ prior to surge	-		16		А
		t = 20 ms	-		140		A
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after	t = 16.7 ms t = 10 ms $I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-		150 98		A A ² s
	triggering	T2+ G+ T2+ G- T2- G- T2- G+	- - -		50 50 50 10		A/μs A/μs A/μs
I _{GM} V _{GM}	Peak gate current Peak gate voltage Peak gate power	12- 0+	- -		2 5 5		A/μs A V W
P _{GM} P _{G(AV)} T _{stg} T _j	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	-40 40		0.5 150 125		°C °C

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 $A/\mu s$.

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 T_{hs} = 25 $^{\circ}$ C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	ı		2500	٧
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	10	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink Thermal resistance	full or half cycle with heatsink compound without heatsink compound in free air	-	- - 55	4.0 5.5	K/W K/W K/W
I ¹ ` th i-a	junction to ambient	III liee all		55		rv, v v

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

,						
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$				
		<u>T</u> 2+ G+	10	14	50	mA
		T2+ G-	10	17	50	mA
		T2- G-	10	18	50	mA
		T2- G+	10	40	100	mA
I ₁	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$				
-	ľ	T2+ G+	-	10	60	mΑ
		T2+ G-	-	25	90	mΑ
		T2- G-	-	12	60	mΑ
		T2- G+	-	14	90	mΑ
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	8	60	mΑ
I I _H V _T	On-state voltage	$I_{T} = 20 \text{ A}$	-	1.2	1.6	V
V _{GT}	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.7	1.5	V
"		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_i = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
I _D	Off-state leakage current	$V_D = V_{DRM(max)}$, $T_j = 125 °C$	-	0.1	0.5	mΑ

DYNAMIC CHARACTERISTICS

 $T_j = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of	V _{DM} = 67% V _{DRM(max)} ; T _j = 125 °C;	200	500	-	V/μs
dV _{com} /dt	off-state voltage Critical rate of change of	exponential waveform; gate open circuit $V_{DM} = 400 \text{ V}; T_j = 95 ^{\circ}\text{C}; I_{T(RMS)} = 16 \text{ A};$	10	20	-	V/μs
t _{gt}	commutating voltage Gate controlled turn-on time	$dI_{com}/dt = 7.2 \text{ A/ms}$; gate open circuit $I_{TM} = 20 \text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1 \text{ A}$; $dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	μs

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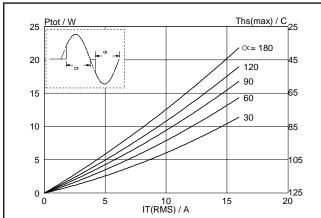


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha = conduction$ angle.

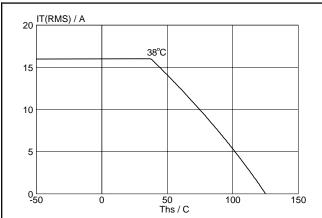


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus heatsink temperature T_{hs} .

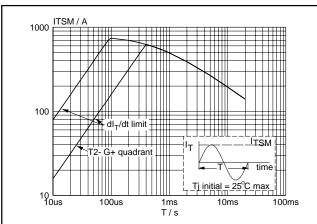


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

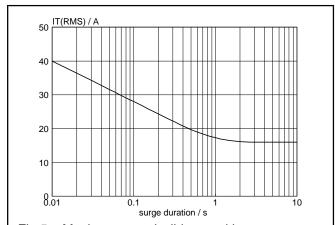


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{hs} \le 38$ °C.

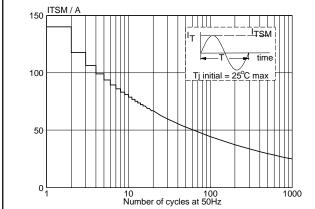


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

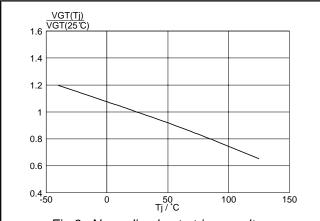
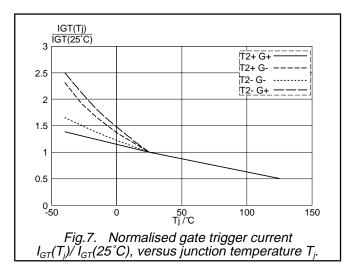
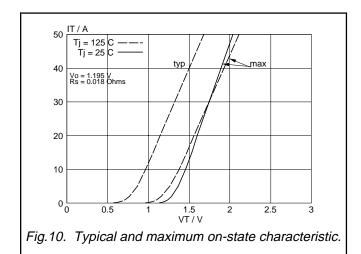
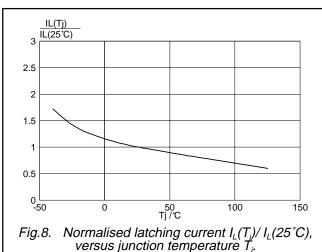


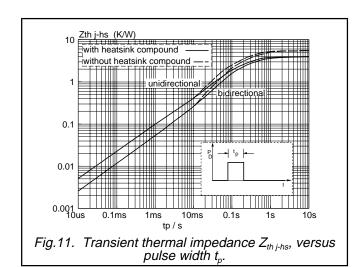
Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature T_j .

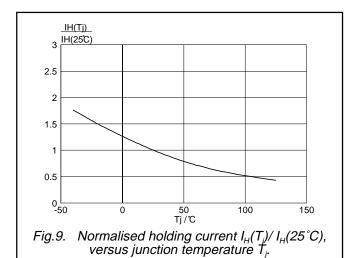
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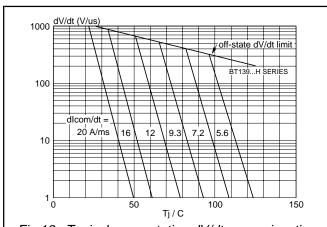
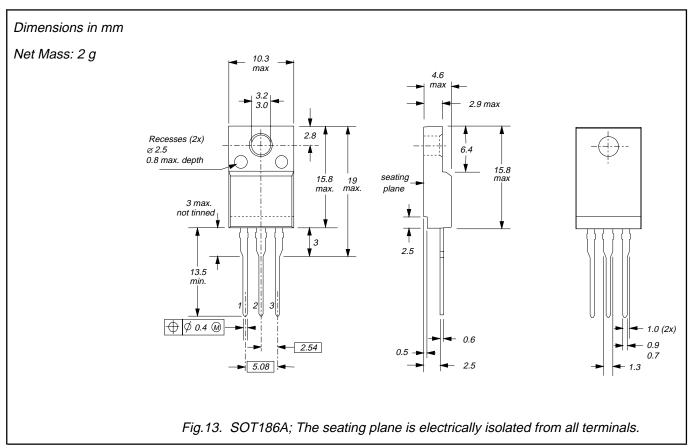


Fig.12. Typical commutation dV/dt versus junction temperature, parameter commutation dl₇/dt. The triac should commutate when the dV/dt is below the value on the appropriate curve for pre-commutation dl₇/dt.

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MECHANICAL DATA



- Refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Triacs high noise immunity

BT139X series H

DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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